

H7N1004AB

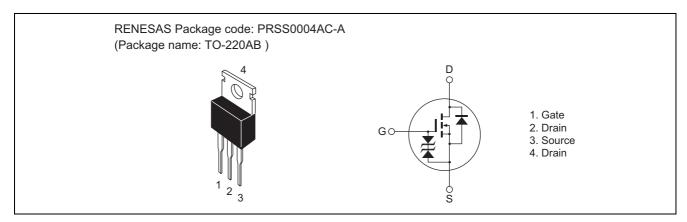
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1579-0100 Rev.1.00 Sep 03, 2007

Features

- Low on-resistance $R_{DS (on)} = 25 \text{ m}\Omega \text{ typ.}$
- Low drive current
- Available for 4.5 V gate drive

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit	
Drain to source voltage	V_{DSS}	100	V	
Gate to source voltage	V _{GSS}	±20	V	
Drain current	I _D	30	A	
Drain peak current	I _{D(pulse)} Note1	100	A	
Body-drain diode reverse drain current	I _{DR}	30	A	
Avalanche current	I _{AP} Note2	15	A	
Avalanche energy	E _{AR} Note2	22.5	mJ	
Channel dissipation	Pch Note3	50	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 ms, duty cycle \leq 1%

2. Value at Tch = 25°C, Rg \geq 50 Ω

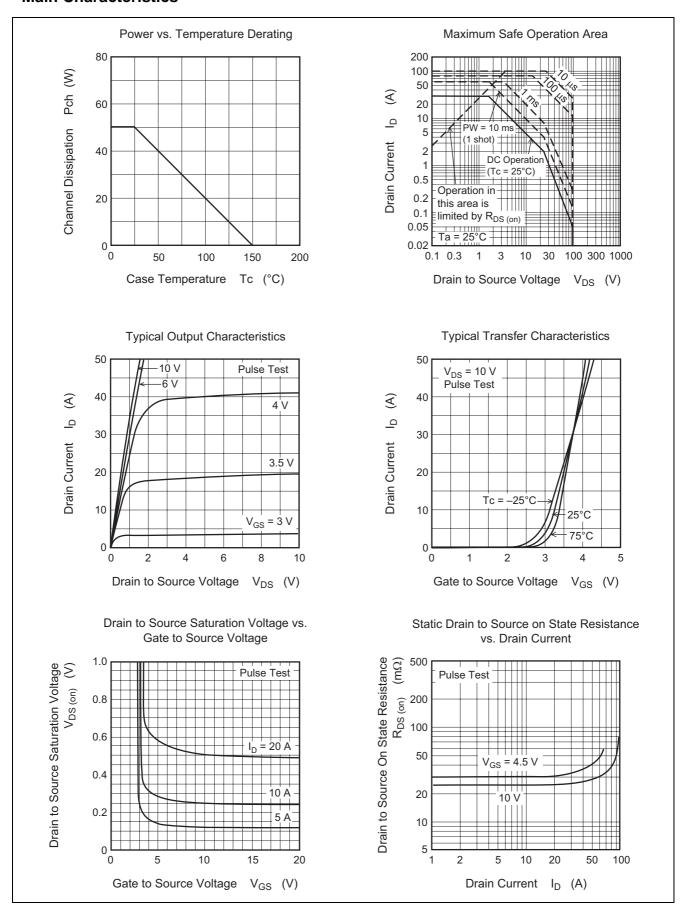
3. Value at Tc = 25°C

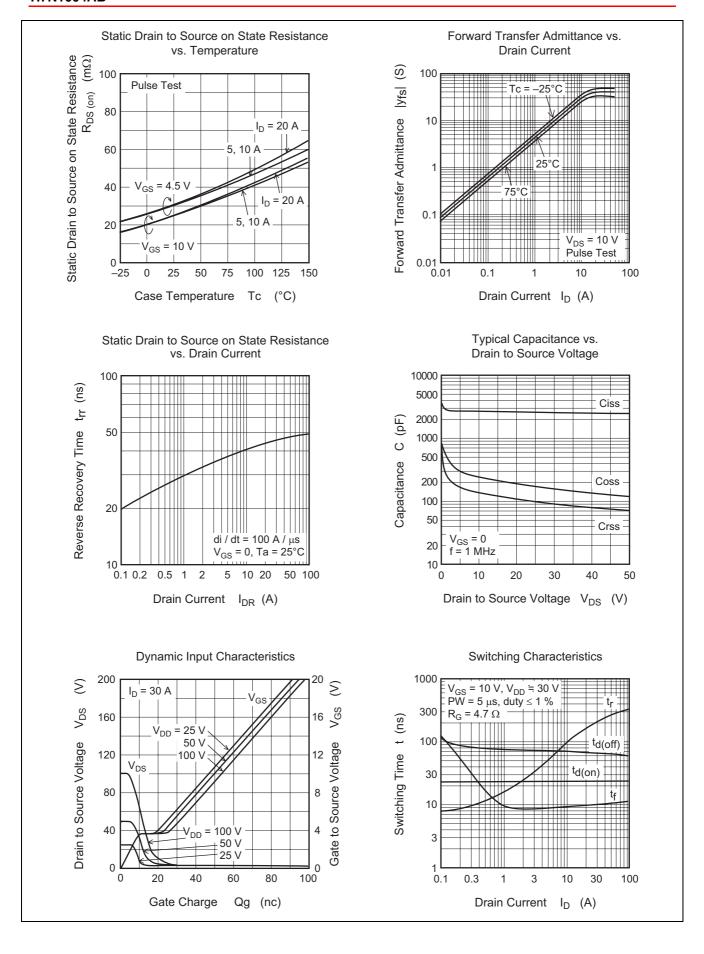
Electrical Characteristics

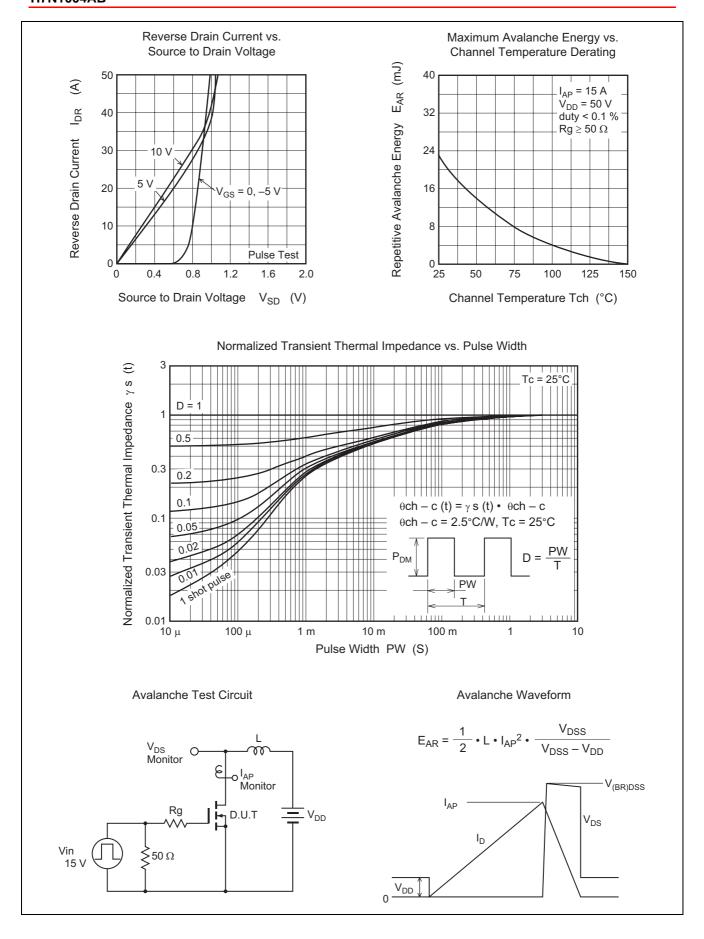
 $(Ta = 25^{\circ}C)$

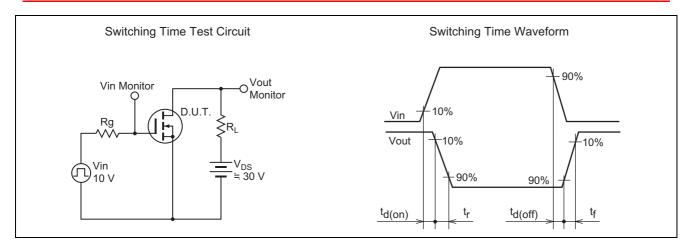
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}		_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	1	_	10	μΑ	$V_{DS} = 100 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	_	2.5	V	$I_D = 1 \text{ mA}, \text{ VDS} = 10 \text{ V}^{\text{Note4}}$
Static drain to source on state	R _{DS(on)}	_	25	35	mΩ	I _D = 15 A, VGS = 10 V Note4
resistance		_	30	45	mΩ	$I_D = 15 \text{ A}, VGS = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	22	37	_	S	$I_D = 15 \text{ A}, \text{ VDS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2800	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	240	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	140	_	pF	f = 1 MHz
Total gate charge	Qg	_	50	_	nC	V _{DD} = 50 V
Gate to source charge	Qgs	_	9	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	11	_	nC	I _D = 30 A
Turn-on delay time	t _{d(on)}	_	23	_	ns	V _{GS} = 10 V, I _D = 15 A
Rise time	t _r	_	120	_	ns	$R_L = 2 \Omega$
Turn-off delay time	t _{d(off)}		70	_	ns	$Rg = 4.7 \Omega$
Fall time	t _f	_	9.5	_	ns	
Body-drain diode forward voltage	V_{DF}		0.9	_	V	I _F = 30 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	_	47	_	ns	$I_F = 30 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Main Characteristics

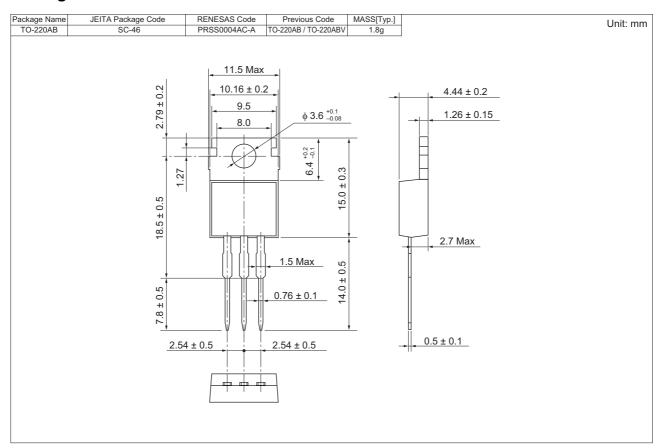








Package Dimensions



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